

深圳市晶泰源电子有限公司

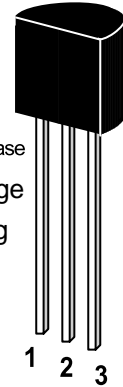
2SA1267

PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into three groups, O, Y and G according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	50	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	50	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_{\text{C}}$	150	mA
Emitter Current	I_{E}	150	mA
Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_{j}	125	$^\circ\text{C}$
Storage Temperature Range	T_{s}	-55 to +125	$^\circ\text{C}$

Characteristics at $T_{\text{amb}}=25^\circ\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{\text{CE}}=6\text{V}$, $-I_{\text{C}}=2\text{mA}$					
Current Gain Group O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
G	h_{FE}	200	-	400	-
Collector Cutoff Current at $-V_{\text{CB}}=50\text{V}$	$-I_{\text{CBO}}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{\text{EB}}=5\text{V}$	$-I_{\text{EBO}}$	-	-	0.1	μA
Collector Emitter Saturation Voltage at $-I_{\text{C}}=100\text{mA}$, $-I_{\text{B}}=10\text{mA}$	$-V_{\text{CE(sat)}}$	-	0.1	0.3	V
Transition Frequency at $-V_{\text{CE}}=10\text{V}$, $-I_{\text{E}}=1\text{mA}$	f_{T}	80	-	-	MHz
Noise Figure at $-V_{\text{CE}}=6\text{V}$, $-I_{\text{C}}=0.1\text{V}$, $f=1\text{KHZ}$, $R_{\text{G}}=10\text{k}\Omega$	NF	-	1	10	dB
Collector Output Capacitance at $-V_{\text{CB}}=10\text{V}$, $f=1\text{MHz}$	C_{OB}	-	4	7	pF